

CLAIM AMENDMENTS:

Please cancel claims 3-4, 6, 14, 16 and 17, so that the status of the claims may be listed as follows:

1. (canceled).
2. (canceled).
3. (canceled).
4. (canceled).
5. (canceled).
6. (canceled).
7. (canceled).
8. (previously presented) A semiconductor device, comprising:
 - a semiconductor chip;
 - an electrode pad formed on the semiconductor chip;
 - a resin film formed to cover a surface of the semiconductor chip;
 - a post bonded to the electrode pad and provided to penetrate through the resin film, a first portion of which in close proximity to a junction portion with the electrode pad is made of gold; and
 - a passivation layer on the surface of the semiconductor chip, between the semiconductor chip and the resin film and covered by the resin film so as to have a passivation film/resin film interface therewith, the gold portion of the post including a portion facing the passivation film/resin film interface, the first portion of the post in direct contact with the passivation film/resin film interface, a second

portion of the post made of a metal material other than gold being separated from the passivation film/resin film interface by the first portion.

9. (canceled).

10. (original) The semiconductor device according to claim 8, wherein the post includes a junction portion provided on a side of the electrode pad and made of gold, a tip end portion provided on a side of a tip end and made of gold, and an intermediate portion provided between the junction portion and the tip end portion and made of a metal material other than gold.

11. (previously presented) The semiconductor device according to claim 8, wherein the passivation layer has a thickness greater than a thickness of the electrode pad and the gold first portion of the post projects below a surface of passivation layer at the passivation film/resin film interface into direct contact with the electrode pad.

12. (previously presented) The semiconductor device according to claim 8, wherein the passivation layer has a thickness greater than a thickness of the electrode pad and the gold first portion of the post projects below a surface of passivation layer at the passivation film/resin film interface into confrontation with the electrode pad.

13. (canceled).

14. (canceled).

15. (original) The semiconductor device according to claim 8, wherein the gold first portion of the post is in direct contact with the electrode pad.

16. (canceled).

17. (canceled).